BYQ72EW-200

Dual ultrafast power diode

14 May 2015 **Product data sheet**

1. General description

Dual ultrafast power diode in a SOT429 (3-lead TO-247) plastic package.

2. Features and benefits

- Very low on-state loss
- Fast switching
- Soft recovery characteristic minimizes power consuming oscillations
- High reverse surge capability
- High thermal cycling performance
- Low thermal resistance

3. Applications

Output rectifiers in high-frequency switched-mode power supplies

4. Quick reference data

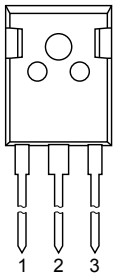
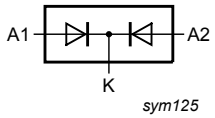
Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{RRM}	repetitive peak reverse voltage			-	-	200	V
$I_{F(AV)}$	average forward current	$\delta = 0.5$; $T_{mb} \leq 113$ °C; square-wave pulse; per diode; Fig. 1; Fig. 2; Fig. 3		-	-	15	A
Static characteristics							
V_F	forward voltage	$I_F = 15$ A; $T_j = 150$ °C; Fig. 6		-	0.78	0.9	V
Dynamic characteristics							
t_{rr}	reverse recovery time	$I_F = 1$ A; $V_R = 30$ V; $dI_F/dt = 100$ A/µs; $T_j = 25$ °C; Fig. 7		-	18	25	ns

Scan or click this QR code to view the latest information for this product

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1	 TO-247 (SOT429)	
2	K	cathode		
3	A2	anode 2		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BYQ72EW-200	TO-247	plastic single-ended through-hole package; heatsink mounted; 1 mounting hole; 3 lead TO-247	SOT429

7. Marking

Table 4. Marking codes

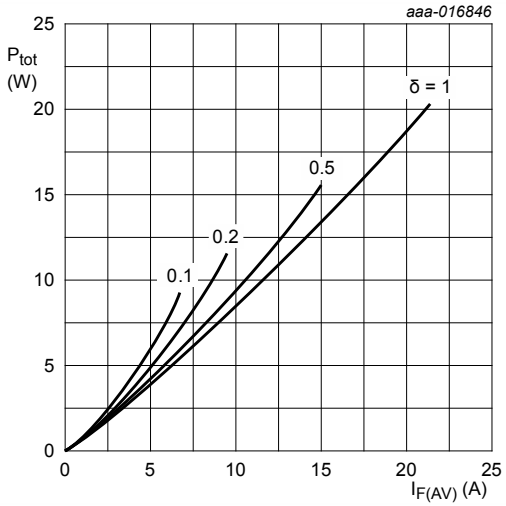
Type number	Marking code
BYQ72EW-200	BYQ72EW-200

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

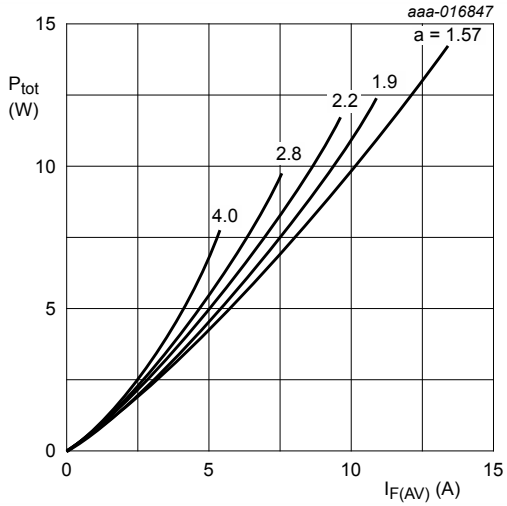
Symbol	Parameter	Conditions		Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage			-	200	V
V_{RWM}	crest working reverse voltage			-	200	V
V_R	reverse voltage	DC		-	200	V
$I_{F(AV)}$	average forward current	δ = 0.5; T_{mb} ≤ 113 °C; square-wave pulse; per diode; Fig. 1; Fig. 2; Fig. 3		-	15	A
$I_{O(AV)}$	average output current	δ = 0.5; T_{mb} ≤ 113 °C; square-wave pulse; both diodes conducting		-	30	A
I_{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4		-	200	A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4		-	220	A
I_{RRM}	repetitive peak reverse current	δ = 0.001; t_p = 2 µs; per diode		-	0.2	A
I_{RSM}	non-repetitive peak reverse current	t_p = 100 µs; per diode		-	0.2	A
T_{stg}	storage temperature			-40	150	°C
T_j	junction temperature			-	150	°C
Electrostatic discharge						
V_{ESD}	electrostatic discharge voltage	HBM; C = 250 pF; R = 1.5 kΩ		-	8	kV



$I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$

$V_o = 0.79$ V; $R_s = 0.008$ Ω

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; per diode; maximum values



a = form factor = $I_{F(RMS)} / I_{F(AV)}$

$V_o = 0.79$ V; $R_s = 0.008$ Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; per diode; maximum values

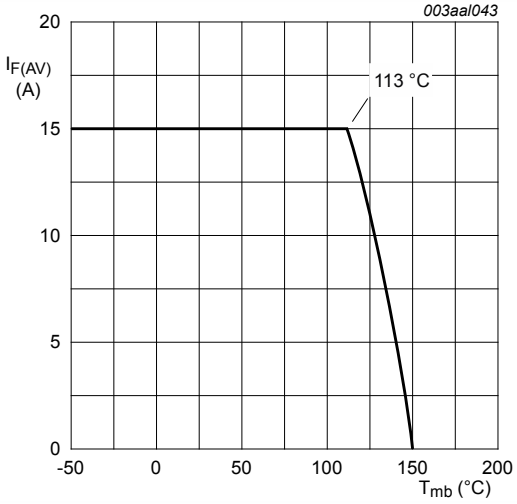


Fig. 3. Average forward current as a function of mounting base temperature; per diode; maximum values

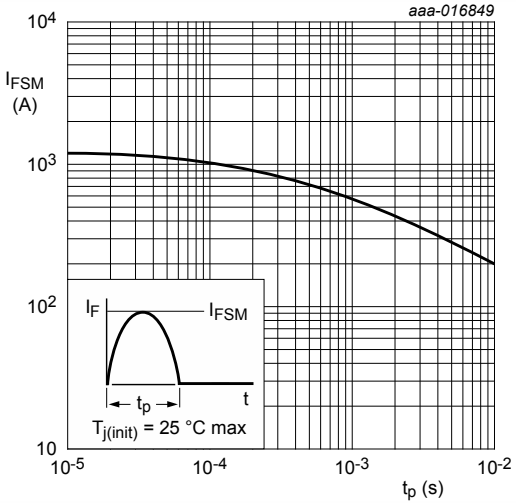


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; per diode; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	with heatsink compound; per diode; Fig. 5		-	1.2	2.4	K/W
		with heatsink compound; both diodes conducting		-	0.7	1.4	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air		-	45	-	K/W

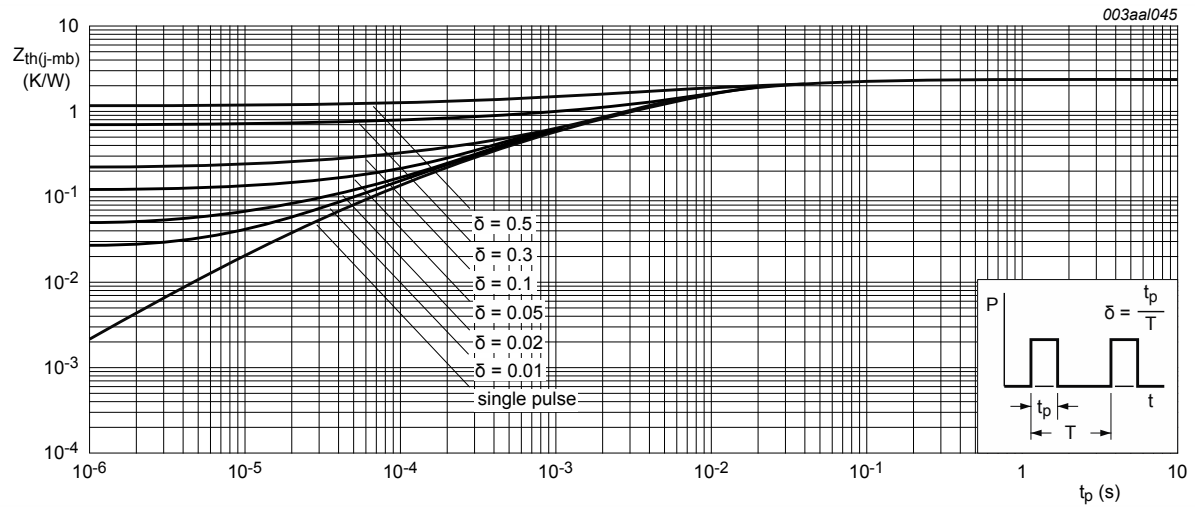


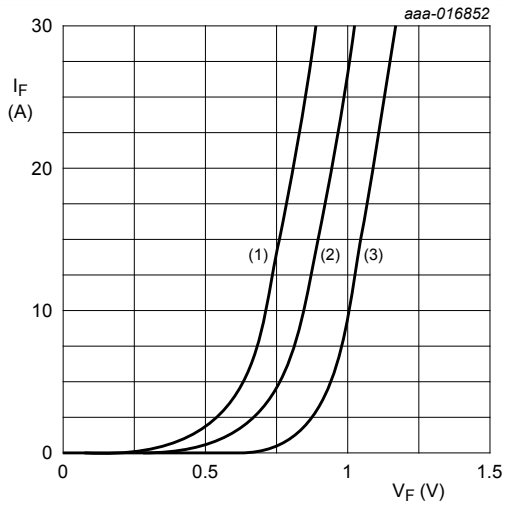
Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse width; per diode; maximum values

10. Characteristics

Table 7. Characteristics

characteristics are per diode unless otherwise stated

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
V_F	forward voltage	I_F = 15 A; T_j = 25 °C; Fig. 6		-	0.95	1.05	V
		I_F = 30 A; T_j = 25 °C; Fig. 6		-	1	1.2	V
		I_F = 15 A; T_j = 150 °C; Fig. 6		-	0.78	0.9	V
I_R	reverse current	V_R = 200 V; T_j = 25 °C		-	3	20	µA
		V_R = 200 V; T_j = 100 °C		-	0.3	1	mA
Dynamic characteristics							
Q_r	recovered charge	I_F = 2 A; V_R = 30 V; dI_F/dt = 20 A/µs; T_j = 25 °C; Fig. 7		-	6	15	nC
		I_F = 1 A; V_R = 30 V; dI_F/dt = 100 A/µs; T_j = 25 °C		-	10	-	nC
t_{rr}	reverse recovery time	I_F = 1 A; V_R = 30 V; dI_F/dt = 100 A/µs; T_j = 25 °C; Fig. 7		-	18	25	ns
I_{RM}	peak reverse recovery current	I_F = 1 A; V_R = 30 V; dI_F/dt = 100 A/µs; T_j = 25 °C		-	1	-	A
V_{FRM}	forward recovery voltage	I_F = 1 A; dI_F/dt = 10 A/µs; T_j = 25 °C; Fig. 8		-	1	-	V



V_o = 0.79 V; R_s = 0.008 Ω

(1) T_j = 150 °C; typical values

(2) T_j = 150 °C; maximum values

(3) T_j = 25 °C; maximum values

Fig. 6. Forward current as a function of forward voltage, per diode

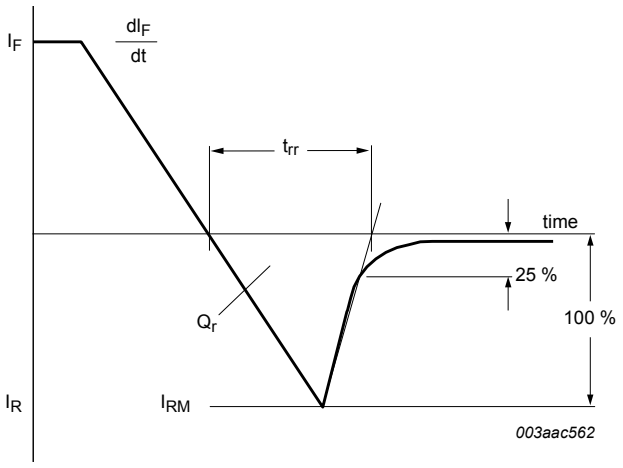


Fig. 7. Reverse recovery definitions; ramp recovery

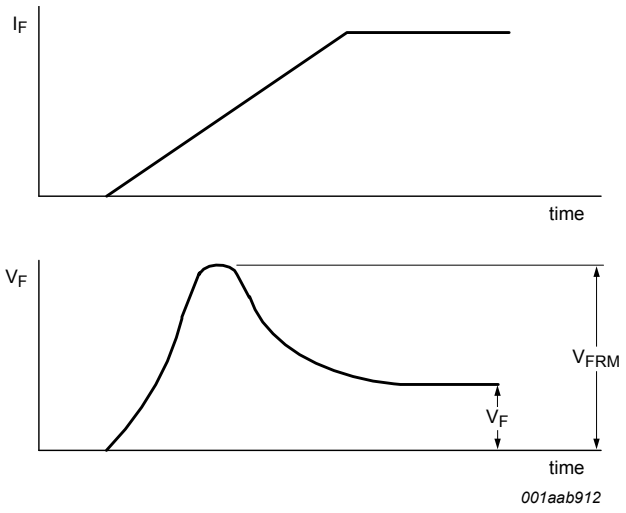
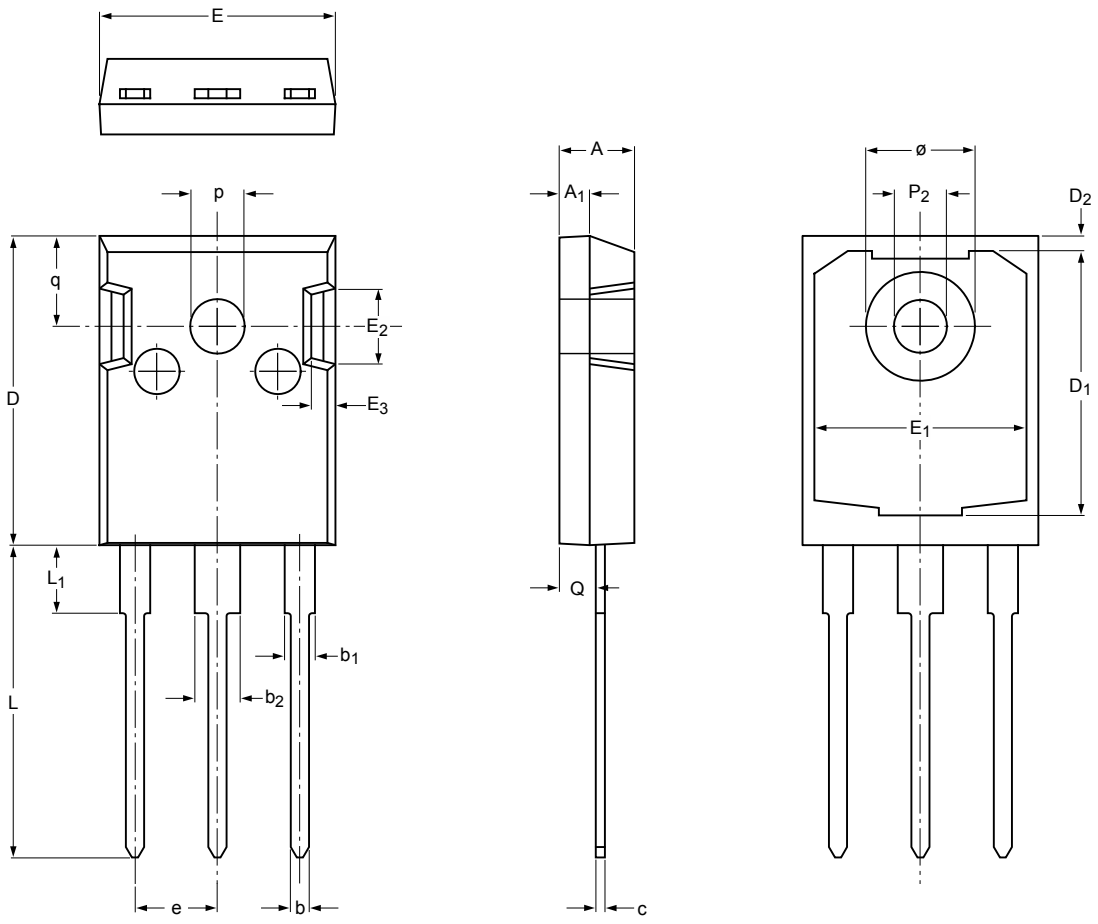


Fig. 8. Forward recovery definitions

11. Package outline

Plastic single-ended through-hole package; heatsink mounted; 1 mounting hole; 3-lead TO-247 **SOT429**



Dimensions (mm are the original dimensions)

Unit[1]		A	A_1	b	b_1	b_2	c	D	D_1	D_2	E	E_1	E_2	E_3	e[1]	L	L_1	P_2	p	Q	q	ø
mm	max	5.20	2.10	1.40	2.20	3.20	0.70	20.6	17.68	1.20	15.75	14.22	5.20	1.80		20.90	4.75	3.60	3.70	2.60	6.18	7.30
	nom														5.45							
	min	4.70	1.90	1.00	1.80	2.80	0.50	20.3	17.28	0.80	15.45	13.82	4.80	1.40		20.40	4.25	3.40	3.50	2.20	5.78	7.10

Note
1. Basic spacing between centers.

sot429_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT429		TO-247				~~04-09-14~~ 13-03-25

Fig. 9. Package outline TO-247 (SOT429)

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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